

ABSTRACT OF THE DISCLOSURE

A polysilicon resistor is formed using a late implant process. Low dopant concentrations on the order of 6×10^{19} to 3.75×10^{20} have shown good results, with a reduced post anneal temperature. Both the first and second order temperature coefficients (TC1 and TC2) can then be adjusted. Using electrical trimming resistors can be produced with highly linear temperature characteristics. By varying the geometries of the resistors, low trimming threshold current densities and voltages can be used to produce good results.

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